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## Small band gap bowing in $\text{In}_{1-x}\text{Ga}_x\text{N}$ alloys

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532	A Study of Indium Nitride Films Grown Under Conditions Resulting in Apparent Band-gaps from 0.7 eV to 2.3 eV. <i>Materials Research Society Symposia Proceedings</i> , <b>2002</b> , 743, L11.23.1		1
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